SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

ABSTRACT

A semiconductor device including a magnetic tunneling junction (MTJ) on a substrate, a first spin orbit torque (SOT) layer on the MTJ, a spacer adjacent to the MTJ and the first SOT layer, and a second SOT layer on the first SOT layer. The first SOT layer and the second SOT layer are made of same material.

Figure 6